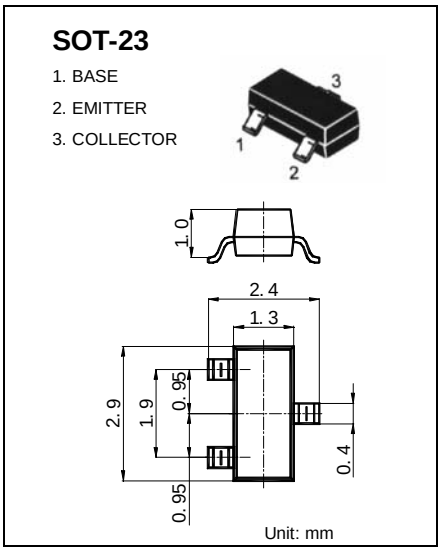
SOT-23 Plastic-Encapsulated Transistors

2SB709A TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM}: 0.2 W (Tamb=25℃)

Collector current

I_{CM}: -0.2 A

Collector-base voltage

$V_{(BR)CBO}$: -45 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= -10 μA, I_E=0	-45		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= -2 mA, I_B=0	-45		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -10 μA, I_C=0	-7		V
Collector cut-off current	I_{CBO}	V_{CB}= -20 V , I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -10 V , I_B=0		-100	μA
DC current gain	h_{FE}	V_{CE}= -10V, I_C= -2mA	160	460	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-100 mA, I_B= -10mA		-0.5	V
Transition frequency	f_T	V_{CE}= -10V, I_C= -1mA f=200MHz	60		MHz

CLASSIFICATION OF H_{FE}

Rank	Q	R	S
Range	160-260	210-340	290-460

Marking	**BR**